

8. (Twice Amended) A system for improving performance in chemical mechanical polishing (CMP) application, comprising:

a wafer head capable of carrying a wafer;

a polishing belt disposed below the wafer head; and

a platen having piezoelectric elements disposed therein, the platen being positioned below the polishing belt, wherein the piezoelectric elements are capable of exerting force on an underside of the polishing belt.

17. (Amended) A method for improving performance in chemical mechanical polishing (CMP) applications, comprising the operations of:

providing a platen having piezoelectric elements disposed therein, the platen being positioned below a polishing belt, wherein the piezoelectric elements are capable of exerting force on an underside of the polishing belt;

applying a wafer to the polishing belt; and

stabilizing the polishing belt utilizing the platen, wherein the piezoelectric elements apply specific forces to the polishing belt.

21. (Amended) A platen for improving performance in chemical mechanical polishing (CMP) applications, comprising:

a plurality of piezoelectric elements disposed in the platen, wherein the plurality of piezoelectric elements is capable of exerting force on an underside of a polishing belt,

wherein each piezoelectric element of the plurality of piezoelectric elements can be individually activated to exert force against the polishing belt, and wherein each piezoelectric element of the plurality of piezoelectric elements can be individually activated to adjust force resistance against the polishing belt.

24. (Amended) A system for improving performance in chemical mechanical polishing (CMP) application, comprising:

a wafer head capable of carrying a wafer;

a polishing belt disposed below the wafer head; and

a platen having piezoelectric elements disposed therein, the platen being positioned below the polishing belt, wherein the piezoelectric elements are capable of exerting force on an underside of the polishing belt, wherein each piezoelectric element can be individually activated to exert force against the polishing belt, and wherein each piezoelectric element can be individually activated to adjust force resistance against the polishing belt; and

a sacrificial material disposed above the platen, the sacrificial material being used to reduce wear on the platen, wherein the sacrificial material is slowly rolled across the platen during a CMP process.